General Purpose Transistors

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: >4000 V
 - Machine Model: >400 V
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}		Vdc
BC846		65	
BC847, BC850		45	
BC848, BC849		30	
Collector-Base Voltage	V_{CBO}		Vdc
BC846		80	
BC847, BC850		50	
BC848, BC849		30	
Emitter-Base Voltage	V _{EBO}		Vdc
BC846		6.0	
BC847, BC850		6.0	
BC848, BC849		5.0	
Collector Current – Continuous	I _C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

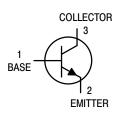
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.



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SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



XX = Device CodeM = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

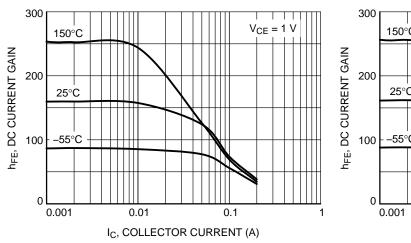
See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Character	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	BC846A, B BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CEO}	65 45 30	- - -	- - -	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A, V_{EB} = 0$)	BC846A, B BC847A, B, C BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CES}	80 50 30	- - -	- - -	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A$)	BC846A, B BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CBO}	80 50 30	- - -	- - -	V
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	BC846A, B BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)EBO}	6.0 6.0 5.0	- - -	- - -	V
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)	I _{CBO}	-	_ _	15 5.0	nA μA	
ON CHARACTERISTICS						
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	h _{FE}	- - -	90 150 270	- - -	-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC846A, BC847A, BC848A BC846B, BC847B, BC848B, BC849B, BC850B 3C847C, BC848C, BC849C, BC850C		110 200	180 290	220 450	
	V _{CE(sat)}	420	520	800		
Collector – Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA)			-	_ _	0.25 0.6	V
Base – Emitter Saturation Voltage ($I_C = 10$ mA, $I_B = 0.5$ mA) ($I_C = 100$ mA, $I_B = 5.0$ mA)				0.7 0.9	_ _	V
Base – Emitter Voltage (I _C = 2.0 mA, V_{CE} = (I _C = 10 mA, V_{CE} =	V _{BE(on)}	580 -	660 -	700 770	mV	
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)			100	_	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)			_	_	4.5	pF
Noise Figure (I_C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω , BC f = 1.0 kHz, BW = 200 Hz)	NF	-	_ _	10 4.0	dB	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846A, BC847A, BC848A, SBC846A



300 150°C VCE = 5 V VCE = 5 V VCE = 5 V 100 25°C 0 0.001 0.01 O.01 IC, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain vs. Collector Current

Figure 2. DC Current Gain vs. Collector Current

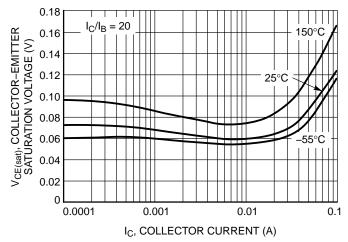


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

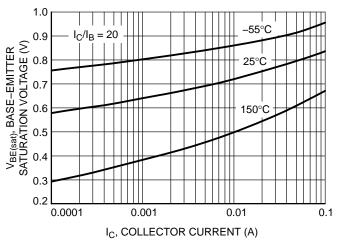


Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

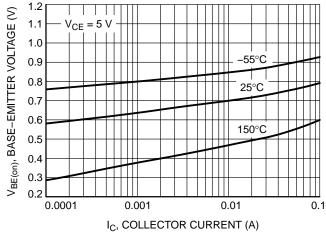


Figure 5. Base Emitter Voltage vs. Collector Current

BC846A, BC847A, BC848A, SBC846A

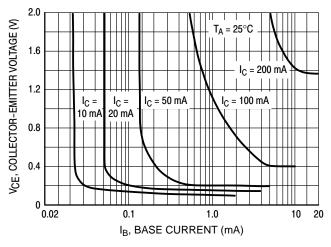


Figure 6. Collector Saturation Region

Figure 7. Base-Emitter Temperature Coefficient

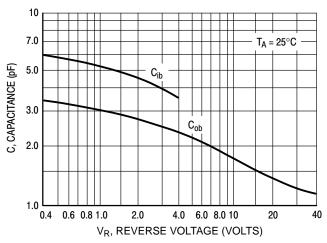


Figure 8. Capacitances

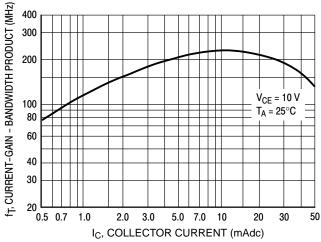
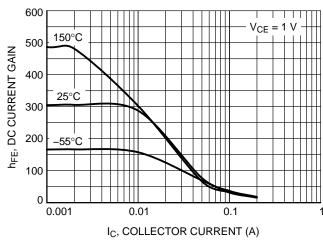


Figure 9. Current-Gain - Bandwidth Product

BC846B, SBC846B



600 $V_{CE} = 5 V$ 150°C 500 h_{FE}, DC CURRENT GAIN 400 25°C 300 200 –55°C 100 0 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

Figure 10. DC Current Gain vs. Collector Current

Figure 11. DC Current Gain vs. Collector Current

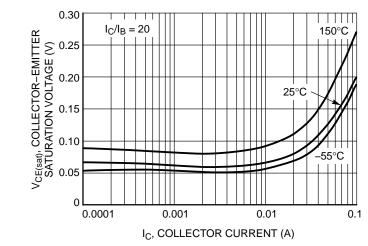


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current

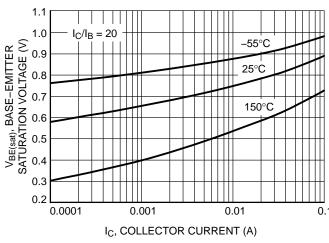


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

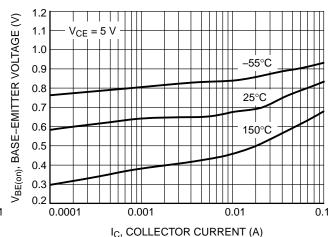


Figure 14. Base Emitter Voltage vs. Collector Current

BC846B, SBC846B

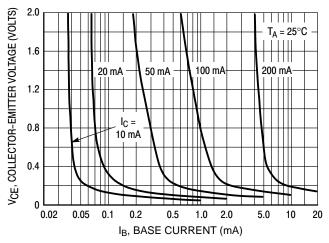
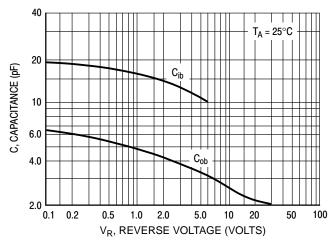


Figure 15. Collector Saturation Region

Figure 16. Base-Emitter Temperature Coefficient





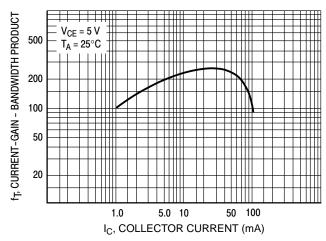
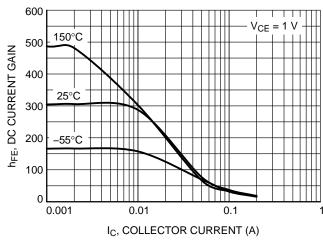


Figure 18. Current-Gain - Bandwidth Product

BC847B, BC848B, BC849B, BC850B, SBC847B, SBC848B



600 $V_{CE} = 5 V$ 150°C 500 h_{FE}, DC CURRENT GAIN 400 25°C 300 200 –55°C 100 0 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

Figure 19. DC Current Gain vs. Collector Current

Figure 20. DC Current Gain vs. Collector Current

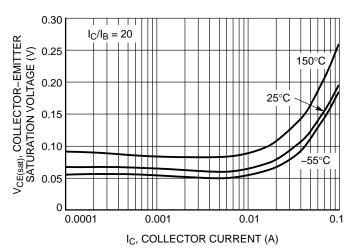


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current

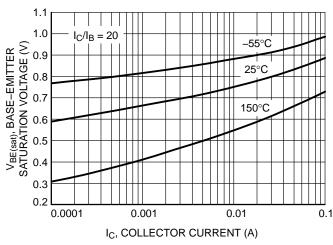


Figure 22. Base Emitter Saturation Voltage vs. Collector Current

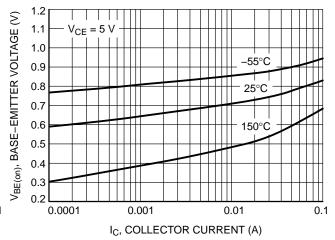


Figure 23. Base Emitter Voltage vs. Collector Current

BC847B, BC848B, BC849B, BC850B, SBC846B, SBC847B, SBC848B

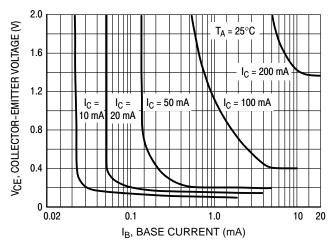


Figure 24. Collector Saturation Region

Figure 25. Base–Emitter Temperature Coefficient

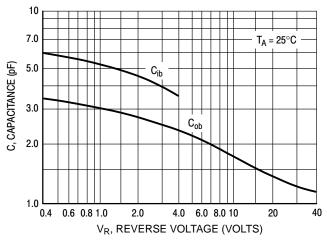


Figure 26. Capacitances

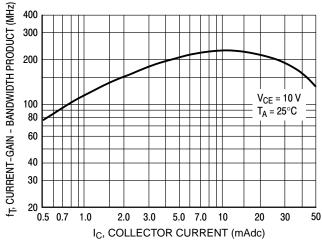
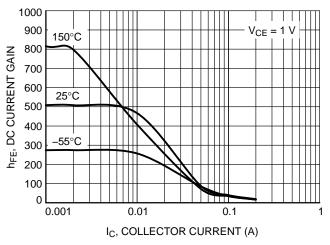


Figure 27. Current-Gain - Bandwidth Product

BC847C, BC848C, BC849C, BC850C, SBC847C



1000 900 150°C 800 hFE, DC CURRENT GAIN 700 600 25°C 500 400 –55°C 300 200 100 0.001 0.1 IC, COLLECTOR CURRENT (A)

Figure 28. DC Current Gain vs. Collector Current

Figure 29. DC Current Gain vs. Collector Current

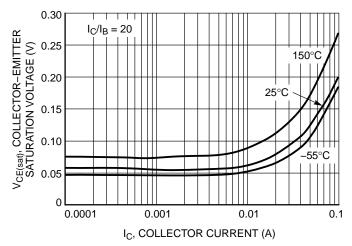
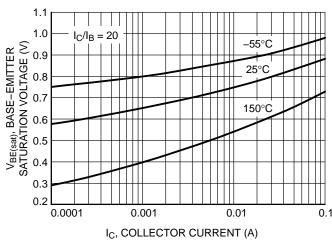


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current



VBE(on), BASE-EMITTER VOLTAGE (V) 1.1 1.0 -55°C 0.9 0.8 25°C 0.7 0.6 150°C 0.5 0.4 0.3 0.2 0.0001 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

Figure 31. Base Emitter Saturation Voltage vs.
Collector Current

Figure 32. Base Emitter Voltage vs. Collector Current

BC847C, BC848C, BC849C, BC850C, SBC847C

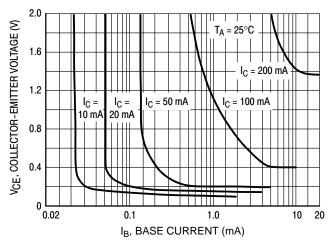
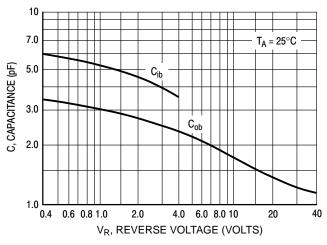


Figure 33. Collector Saturation Region

Figure 34. Base–Emitter Temperature Coefficient





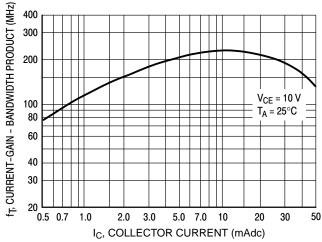


Figure 36. Current-Gain - Bandwidth Product

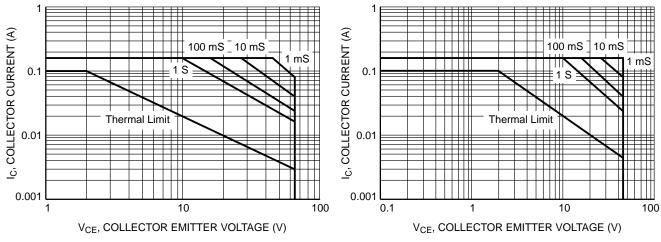


Figure 37. Safe Operating Area for BC846A, BC846B

Figure 38. Safe Operating Area for BC847A, BC847B, BC847C, BC850B, BC850C

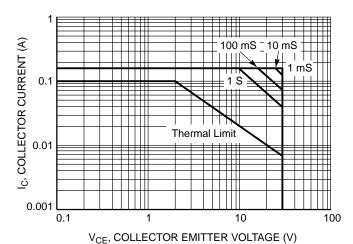


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C, BC849B, BC849C

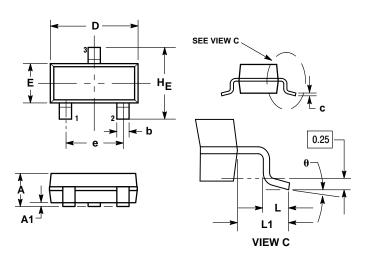
ORDERING INFORMATION

Device	Marking	Package	Shipping [†]		
BC846ALT1G	1A	SOT-23	3,000 / Tape & Reel		
SBC846ALT1G*	TA TA	(Pb-Free)	5,000 / Tape & Reel		
BC846ALT3G	1A	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC846BLT1G	1B	SOT-23	2 000 / Tana & Paol		
SBC846BLT1G*	IB	(Pb-Free)	3,000 / Tape & Reel		
BC846BLT3G	1B	SOT-23	10 000 / Tono & Book		
SBC846BLT3G*	(Pb–Free)		10,000 / Tape & Reel		
BC847ALT1G	1E	SOT-23 (Pb-Free)	3,000 / Tape & Reel		
BC847ALT3G	15	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC847BLT1G	45	SOT-23	0.000 /T-r- 0.D1		
SBC847BLT1G*	1F	(Pb-Free)	3,000 / Tape & Reel		
BC847BLT3G	45	SOT-23	40,000 / Tong % Book		
NSVBC847BLT3G*	1F	(Pb-Free)	10,000 / Tape & Reel		
BC847CLT1G	10	SOT-23	2 000 / Tana & Baal		
SBC847CLT1G*	1G	(Pb-Free)	3,000 / Tape & Reel		
BC847CLT3G	1G	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC848ALT1G	1J	SOT-23 (Pb-Free)	3,000 / Tape & Reel		
BC848BLT1G		SOT-23	/-		
SBC848BLT1G*	1K	(Pb-Free)	3,000 / Tape & Reel		
BC848BLT3G	1K	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC848CLT1G		SOT-23 (Pb-Free)	3,000 / Tape & Reel		
BC848CLT3G	1L	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC849BLT1G	0.0	SOT-23 (Pb-Free)	3,000 / Tape & Reel		
BC849BLT3G	2B	SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC849CLT1G		SOT-23 (Pb-Free)	3,000 / Tape & Reel		
BC849CLT3G	2C 2S49CLT3G		10,000 / Tape & Reel		
BC850BLT1G	2F	SOT-23 (Pb-Free)	0.000 / To - 0.75		
BC850CLT1G	2G	SOT-23 (Pb-Free)	3,000 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AP**



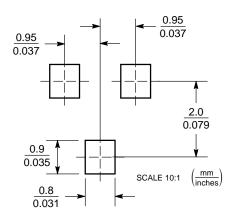
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°		10°	0°		10°

- STYLE 6: PIN 1. BASE
 - 2. **EMITTER**
 - COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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